



# STB140NF55 - STB140NF55-1 STP140NF55

N-channel 55V - 0.0065Ω - 80A - D<sup>2</sup>PAK - I<sup>2</sup>PAK - TO-220  
STripFET™ II Power MOSFET

## General features

Type	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub> <sup>(1)</sup>
STB140NF55	55V	<0.008Ω	80A
STB140NF55-1	55V	<0.008Ω	80A
STP140NF55	55V	<0.008Ω	80A

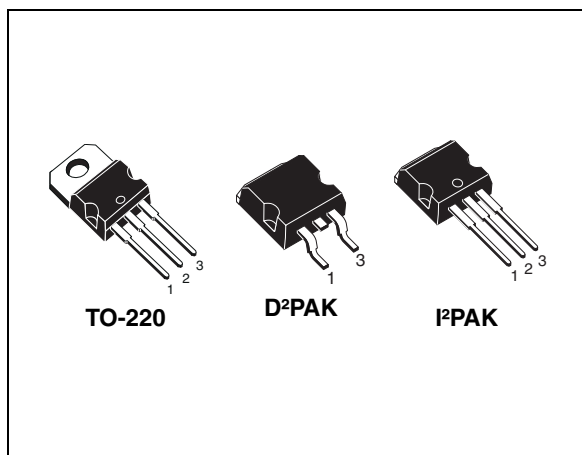
1. Current limited by package

## Description

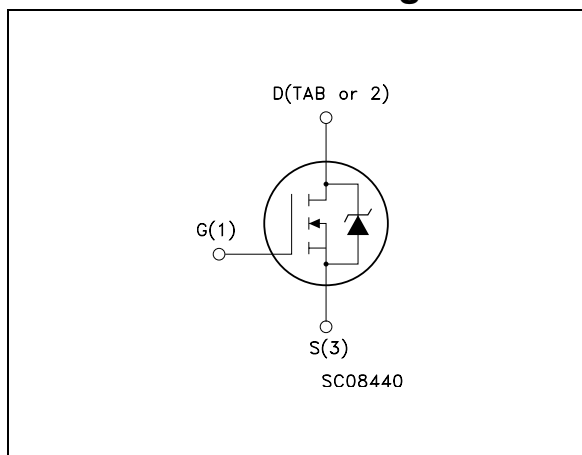
This Power MOSFET is the latest development of STMicroelectronics unique “Single Feature Size™” strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

## Applications

- Motor control
- High current, switching application



## Internal schematic diagram



## Order codes

Part number	Marking	Package	Packaging
STB140NF55	B140NF55	D <sup>2</sup> PAK	Tape & reel
STB140NF55-1	B140NF55	I <sup>2</sup> PAK	Tube
STP140NF55	P140NF55	TO-220	Tube

# Contents

<b>1</b>	<b>Electrical ratings</b> .....	<b>3</b>
<b>2</b>	<b>Electrical characteristics</b> .....	<b>4</b>
2.1	Electrical characteristics (curves) .....	6
<b>3</b>	<b>Test circuit</b> .....	<b>8</b>
<b>4</b>	<b>Package mechanical data</b> .....	<b>9</b>
<b>5</b>	<b>Packaging mechanical data</b> .....	<b>13</b>
<b>6</b>	<b>Revision history</b> .....	<b>14</b>

# 1 Electrical ratings

**Table 1. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source voltage ( $V_{GS} = 0$ )	55	V
$V_{GS}$	Gate- source voltage	$\pm 20$	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25^\circ\text{C}$	80	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100^\circ\text{C}$	80	A
$I_{DM}^{(2)}$	Drain current (pulsed)	320	A
$P_{TOT}$	Total dissipation at $T_C = 25^\circ\text{C}$	300	W
	Derating factor	2	W/ $^\circ\text{C}$
$dv/dt^{(3)}$	Peak diode recovery voltage slope	10	V/ns
$E_{AS}^{(4)}$	Single pulse avalanche energy	1.3	J
$T_{stg}$	Storage temperature	-55 to 175	$^\circ\text{C}$
$T_j$	Operating junction temperature		

1. Current limited by package
2. Pulse width limited by safe operating area
3.  $I_{SD} \leq 80\text{A}$ ,  $di/dt \leq 300\text{A}/\mu\text{s}$ ,  $V_{DD} = 80\%V_{(BR)DSS}$
4. Starting  $T_j = 25^\circ\text{C}$ ,  $I_D = 40\text{A}$ ,  $V_{DD} = 30\text{V}$

**Table 2. Thermal data**

Symbol	Parameter	Value		Unit
		TO-220 - I <sup>2</sup> PAK	D <sup>2</sup> PAK	
$R_{thj-case}$	Thermal resistance junction-case max	0.5		$^\circ\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-ambient max	62.5	--	$^\circ\text{C}/\text{W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb max	--	35	$^\circ\text{C}/\text{W}$
$T_l$	Maximum lead temperature for soldering purpose (for 10 sec, 1.6mm from case)	300		$^\circ\text{C}$

1. When mounted on 1 inch<sup>2</sup>, FR4 board, 2 oz Cu

## 2 Electrical characteristics

( $T_{CASE}=25^{\circ}\text{C}$  unless otherwise specified)

**Table 3. On/off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250 \mu\text{A}$ , $V_{GS} = 0$	55			V
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS} = 0$ )	$V_{DS} = \text{Max rating}$ $V_{DS} = \text{Max rating}$ , $T_C = 125^{\circ}\text{C}$			1 10	$\mu\text{A}$ $\mu\text{A}$
$I_{GSS}$	Gate-body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 20\text{V}$			$\pm 100$	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 250\mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10 \text{ V}$ , $I_D = 40 \text{ A}$		0.0065	0.008	$\Omega$

**Table 4. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} = 15\text{V}$ , $I_D = 40 \text{ A}$		100		S
$C_{iss}$	Input capacitance	$V_{DS} = 25\text{V}$ , $f = 1 \text{ MHz}$ $V_{GS} = 0$		5300		pF
$C_{oss}$	Output capacitance			1000		pF
$C_{rss}$	Reverse transfer capacitance			290		pF
$Q_g$	Total gate charge	$V_{DD} = 44\text{V}$ , $I_D = 80\text{A}$		142		nC
$Q_{gs}$	Gate-source charge	$V_{GS} = 10\text{V}$		27		nC
$Q_{gd}$	Gate-drain charge	(see Figure 14)		55		nC

1. Pulsed: pulse duration = 300 $\mu\text{s}$ , duty cycle 1.5%

**Table 5. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ $t_r$	Turn-on delay time Rise time	$V_{DD} = 27.5\text{ V}$ , $I_D = 40\text{ A}$ $R_G = 4.7\Omega$ , $V_{GS} = 10\text{ V}$ (see Figure 13)		30 150		ns ns
$t_{d(off)}$ $t_f$	Turn-off-delay time Fall time	$V_{DD} = 27.5\text{ V}$ , $I_D = 40\text{ A}$ , $R_G = 4.7\Omega$ , $V_{GS} = 10\text{ V}$ (see Figure 13)		125 45		ns ns

**Table 6. Source drain diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current				80	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				320	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 80\text{ A}$ , $V_{GS} = 0$			1.5	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 80\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD} = 20\text{ V}$ , $T_j = 150^\circ\text{C}$ (see Figure 15)		90		ns
$Q_{rr}$	Reverse recovery charge			275		nC
$I_{RRM}$	Reverse recovery current			6.5		A

1. Pulse width limited safe operating area
2. Pulsed: pulse duration = 300 $\mu\text{s}$ , duty cycle 1.5%

## 2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

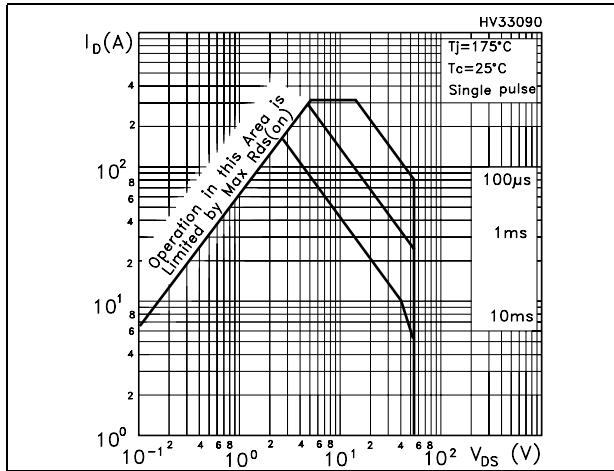


Figure 2. Thermal impedance

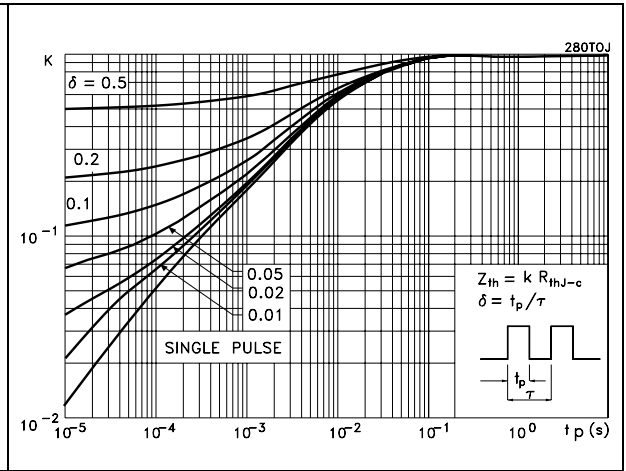


Figure 3. Output characteristics

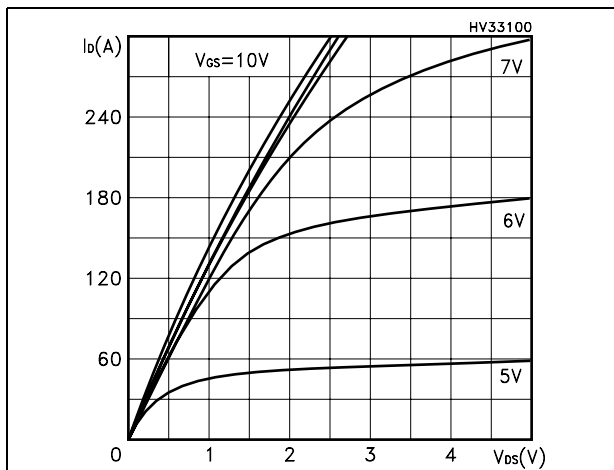


Figure 4. Transfer characteristics

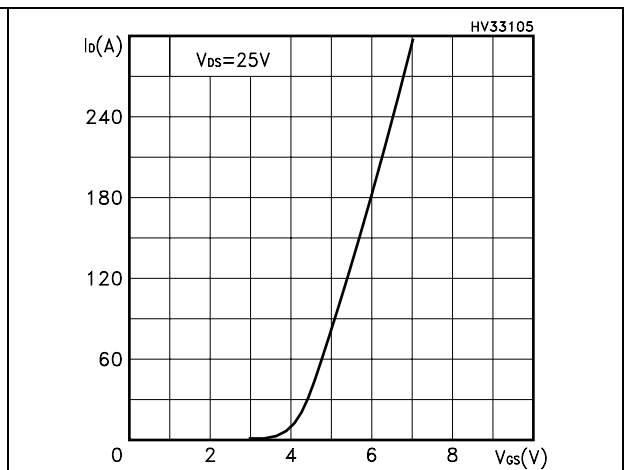


Figure 5. Transconductance

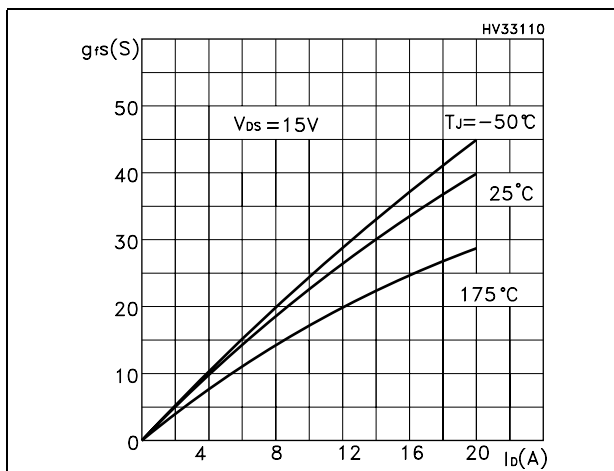


Figure 6. Static drain-source on resistance

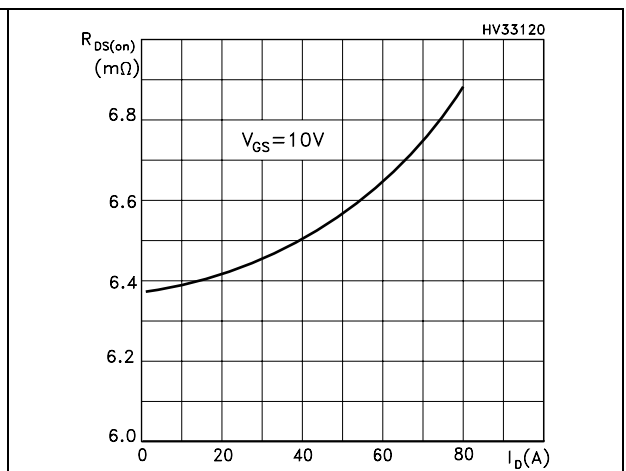


Figure 7. Gate charge vs gate-source voltage Figure 8. Capacitance variations

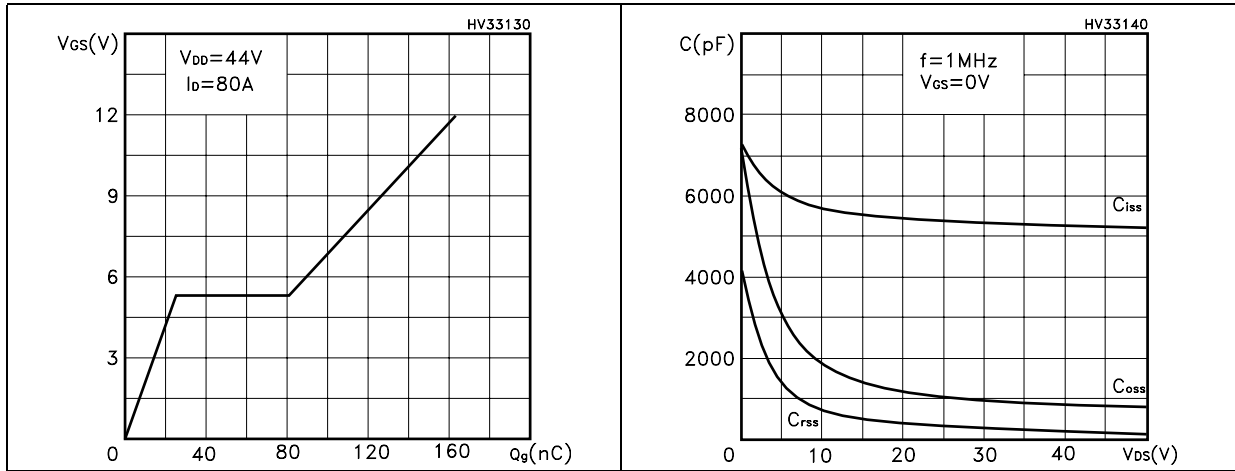


Figure 9. Normalized gate threshold voltage vs temperature

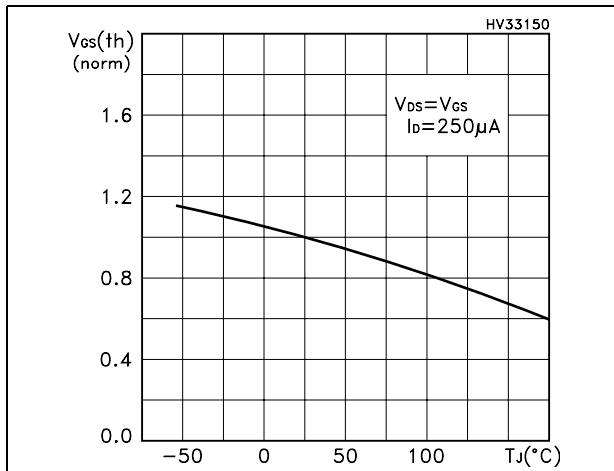


Figure 10. Normalized on resistance vs temperature

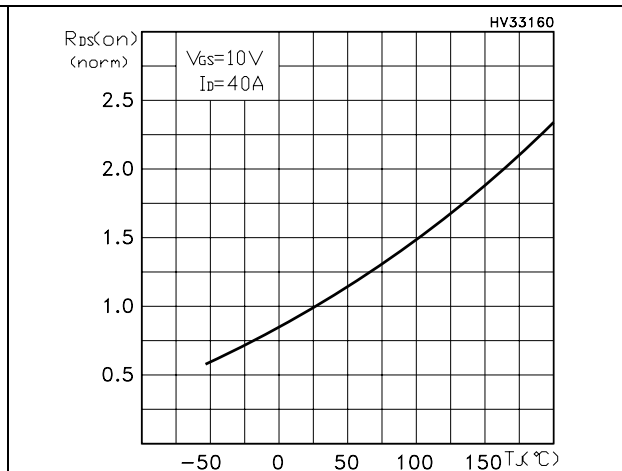


Figure 11. Source-drain diode forward characteristics

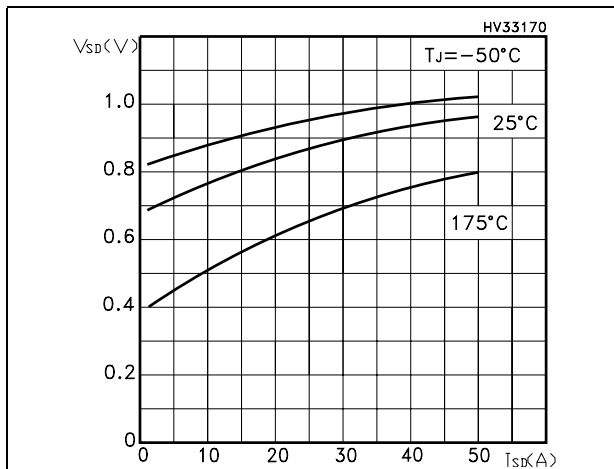
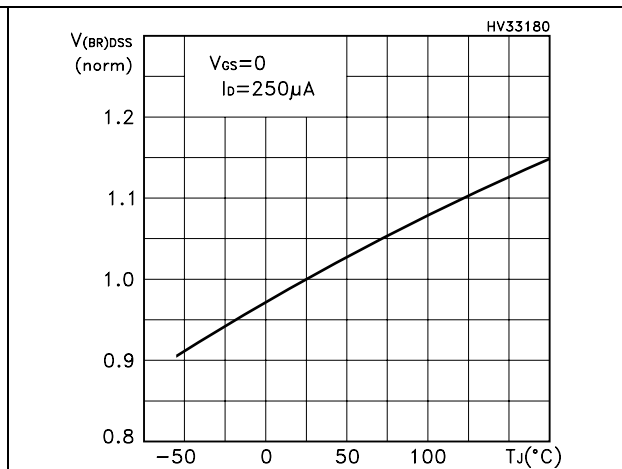


Figure 12. Normalized  $B_{V_{DS}}$  vs temperature



### 3 Test circuit

Figure 13. Switching times test circuit for resistive load

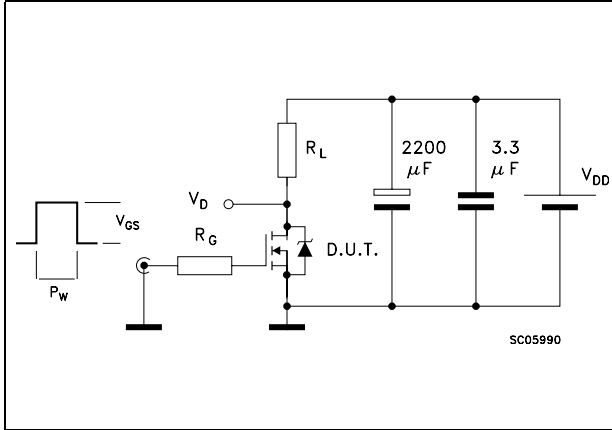


Figure 14. Gate charge test circuit

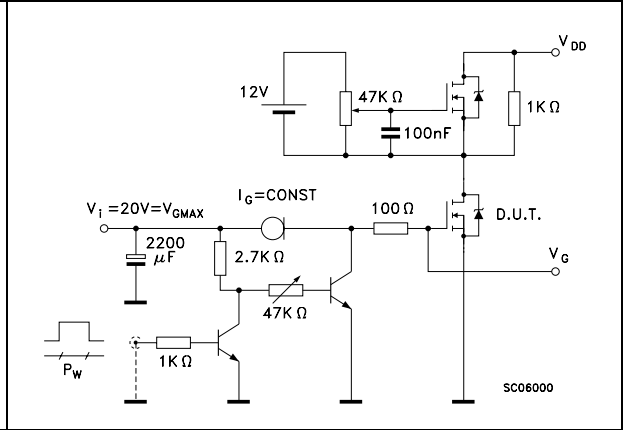


Figure 15. Test circuit for inductive load switching and diode recovery times

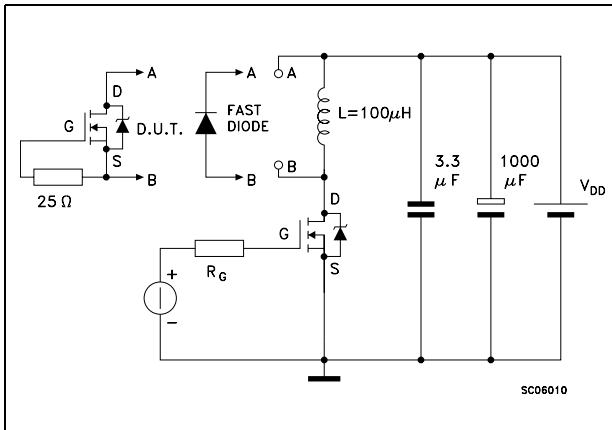


Figure 16. Unclamped inductive load test circuit

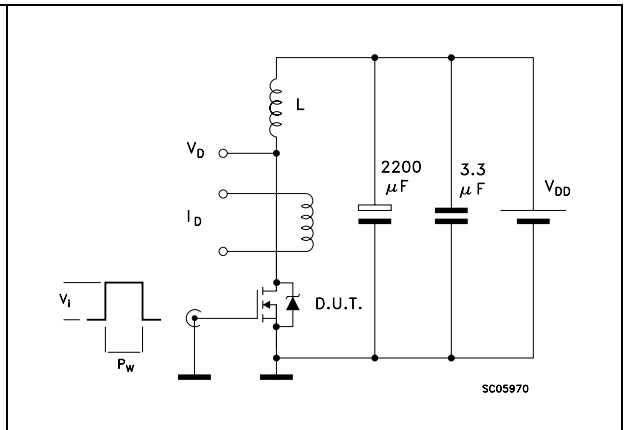
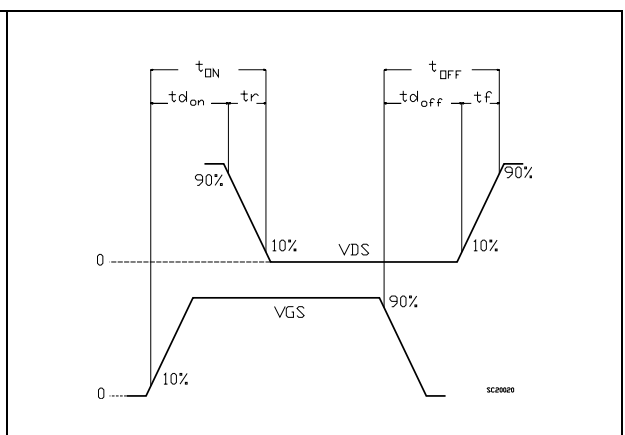


Figure 17. Unclamped inductive waveform



Figure 18. Switching time waveform



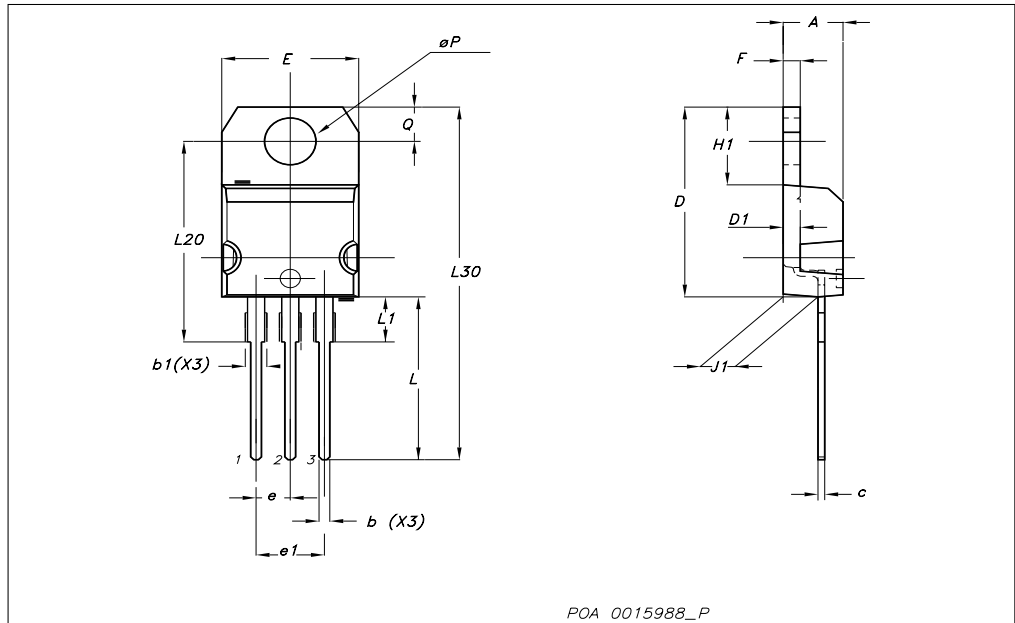


## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: [www.st.com](http://www.st.com)

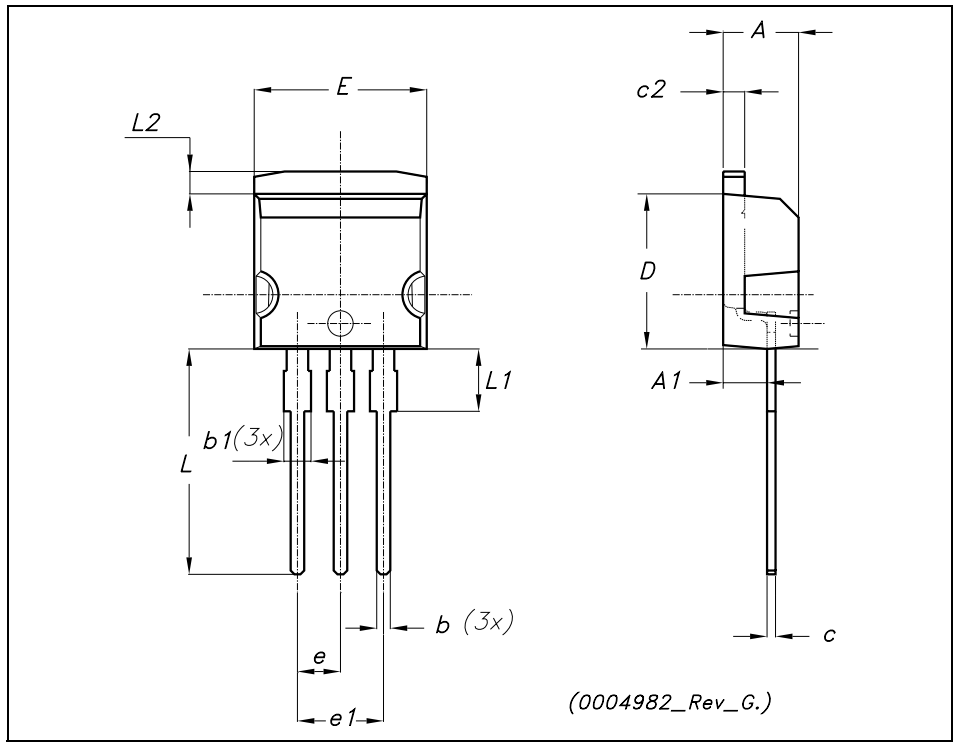
**TO-220 mechanical data**

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.6		0.62
D1		1.27			0.050	
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.051
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
ØP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



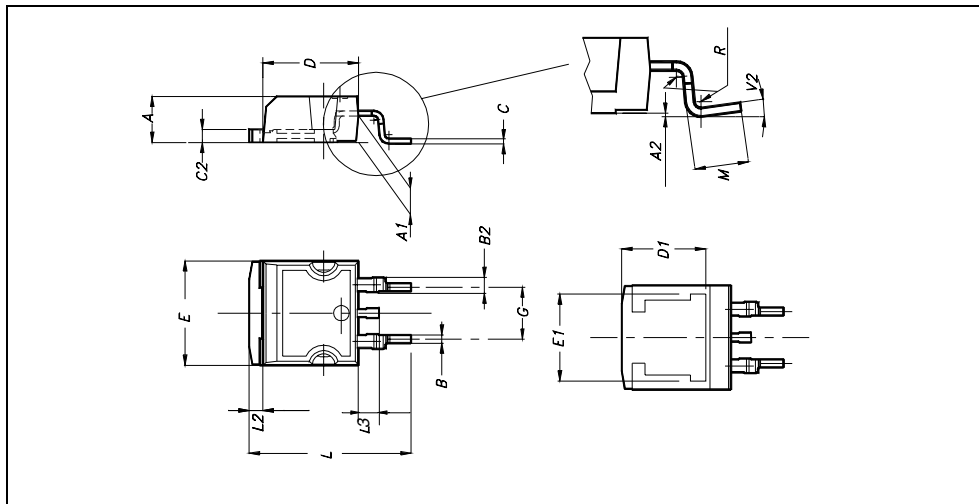
**TO-262 (I<sup>2</sup>PAK) MECHANICAL DATA**

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
A1	2.40		2.72	0.094		0.107
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.49		0.70	0.019		0.027
c2	1.23		1.32	0.048		0.052
D	8.95		9.35	0.352		0.368
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
E	10		10.40	0.393		0.410
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L2	1.27		1.40	0.050		0.055



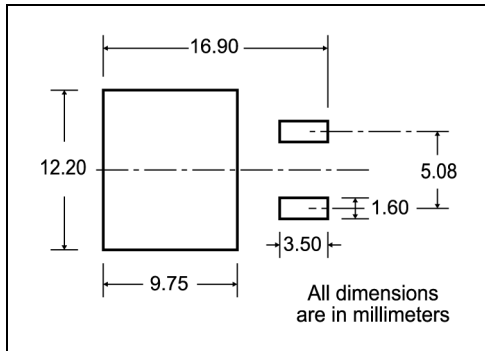
**D<sup>2</sup>PAK MECHANICAL DATA**

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0°		4°			



# 5 Packaging mechanical data

## D<sup>2</sup>PAK FOOTPRINT



## TAPE AND REEL SHIPMENT

40 mm min. Access hole at slot location

Full radius

Tape slot in core for tape start 2.5mm min. width

G measured at hub

### REEL MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197

### TAPE MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956

TOP COVER TAPE

User Direction of Feed

Center line of cavity

R min.

Bending radius

FEED DIRECTION

\* on sales type

## 6 Revision history

Table 7. Revision history

Date	Revision	Changes
07-Dec-2004	1	Initial release.
07-Apr-2006	2	Updated <a href="#">Figure 8</a>
04-Aug-2006	3	New template, modified <a href="#">Figure 1</a>
02-Mar-2007	4	Applications have been updated

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